Development of an Infrastructure for the Growth and Characterization of GaN on Nitrided Sapphire

Thesis

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By
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Abstract

A custom ultrahigh vacuum chamber was constructed suitable for study of GaN growth kinetics. Design modifications have been made in this growth chamber to allow for growth of GaN under a wide range of conditions. The ion content from a rf-plasma source was studied and controlled for future nitridation of sapphire experiments. It was shown to be possible to both decrease and increase the ion content from the source. A temperature dependent Hall effect measurement set-up was implemented. The set up was tested using as-grown samples and shown to be an effective way of determining the electrical properties of semiconductors. Future areas of research relying on the infrastructure created herein are outlined.
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Table of Contents

Abstract........................................................................................................................................... ii

Acknowledgments.......................................................................................................................... iii

Table of Contents........................................................................................................................... iv

List of Figures................................................................................................................................ vi

Chapter

1. Introduction........................................................................................................................1
  1.1 Wide Bandgap Semiconductor Technology ............................................................1
  1.2 Gallium Nitride........................................................................................................3
  1.3 Nitridation of Sapphire ............................................................................................5
  1.4 Goals and Motivation ..............................................................................................7

2. GaN Growth Chamber with Desorption Mass Spectrometry Capabilities...............9
  2.1 Growth Chamber .....................................................................................................9
    2.1.1 System Requirements...................................................................................9
    2.1.2 Chamber Design.........................................................................................11
  2.2 Desorption Mass Spectrometry..............................................................................17
    2.2.1 Growth Kinetics.........................................................................................17
    2.2.2 Desorption Mass Spectrometry and Growth Kinetics ...............................24
    2.2.3 Desorption Mass Spectrometry Setup........................................................27

3. N$_2$ Source: Characterization and Control of Nitrogen Ion Content ......................33
  3.1 Source Description.................................................................................................33
  3.2 Experimental Setup.................................................................................................35
4. Temperature Dependent Hall Measurements ...............................................................53
   4.1 Electrical Properties of Semiconductors ..............................................................53
   4.1.1 Free Electron Model ....................................................................................53
   4.1.2 Quantum Mechanical Model .......................................................................54
   4.2 Hall Effect in Semiconductors ...........................................................................58
   4.3 Experimental Setup ..........................................................................................61
   4.4 Results .............................................................................................................64
5. Future Areas of Research .........................................................................................72
   5.1 Nitridation of Sapphire .....................................................................................72
   5.2 GaN Grown on Nitrided Sapphire ....................................................................72
   5.3 Electrical Characterization of GaN Grown on Nitrided Sapphire .......................73
# List of Figures

<table>
<thead>
<tr>
<th>Figure</th>
<th>Description</th>
<th>Page</th>
</tr>
</thead>
<tbody>
<tr>
<td>2.1</td>
<td>General external MBE2 design schematic</td>
<td>12</td>
</tr>
<tr>
<td>2.2</td>
<td>EPI designed substrate heater</td>
<td>13</td>
</tr>
<tr>
<td>2.3</td>
<td>General internal MBE2 chamber design schematic</td>
<td>15</td>
</tr>
<tr>
<td>2.4</td>
<td>Schematic diagram of processes involved in film nucleation and growth</td>
<td>18</td>
</tr>
<tr>
<td>2.5a</td>
<td>AFM image of prismatic hillock features</td>
<td>20</td>
</tr>
<tr>
<td>2.5b</td>
<td>TEM image of inversion domains and prismatic hillock features</td>
<td>21</td>
</tr>
<tr>
<td>2.5c</td>
<td>TEM image of inversion domains and prismatic hillock features (close up)</td>
<td>22</td>
</tr>
<tr>
<td>2.6a</td>
<td>Growth rate vs. Ga flux, with and without hydrogen</td>
<td>23</td>
</tr>
<tr>
<td>2.6b</td>
<td>Growth rate vs. growth temperature, with and without hydrogen</td>
<td>25</td>
</tr>
<tr>
<td>2.7</td>
<td>DMS schematic diagram</td>
<td>28</td>
</tr>
<tr>
<td>2.8</td>
<td>Schematic diagram of QMS system</td>
<td>29</td>
</tr>
<tr>
<td>3.1</td>
<td>Oxford Applied Research CARS25 Radical Beam source for the production of atomic nitrogen</td>
<td>34</td>
</tr>
<tr>
<td>3.2</td>
<td>WVU Chemical Engineering Chamber used to study nitrogen source</td>
<td>36</td>
</tr>
<tr>
<td>3.3</td>
<td>Schematic of bias grid setup</td>
<td>37</td>
</tr>
<tr>
<td>3.4</td>
<td>Schematic of bias plate setup</td>
<td>39</td>
</tr>
<tr>
<td>3.5</td>
<td>Schematic of substrate bias</td>
<td>40</td>
</tr>
<tr>
<td>3.6</td>
<td>Bias grid setup, current vs. bias voltage</td>
<td>41</td>
</tr>
</tbody>
</table>
Figure 3.7 Bias grid setup, mass spec. vs. bias voltage ...........................................................43
Figure 3.8 Bias plate setup, current vs. bias voltage ...............................................................44
Figure 3.9 Bias plate setup, mass spec. vs. bias voltage .........................................................46
Figure 3.10 Mass spectrometer and current data plotted as a function of bias voltage ..........48
Figure 3.11 Mass spectrometer measured intensity vs. ion energy of N+ for three different bias plate conditions ..........................................................50
Figure 3.12 Mass spectrometer measured intensity vs. ion energy of N2+ for three different bias plate conditions ..........................................................51
Figure 4.1 Semiconductor band structure schematic ..............................................................55
Figure 4.2 Hall effect measurement schematic .......................................................................59
Figure 4.3 Van der Pauw geometry schematic and basic Hall equations ..................................62
Figure 4.4 Weighting function distribution across sample with corner contacts ......................63
Figure 4.5 Temperature dependent Hall effect measurement setup schematic .....................65
Table 4.1 Room temperature Hall results for various samples grown by WVU MBE Laboratory ...........................................................67
Figure 4.6 Temperature dependence of resistivity for a CdGeAs2 sample ..............................68
Figure 4.7 Temperature dependence of carrier concentration for a CdGeAs2 sample ..............69
Figure 4.8 Temperature dependence of mobility for a CdGeAs2 sample ..................................71